



P-Channel Enhancement Mode Power MOSFET

Description

The PE7290G uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. It can be used in a wide variety of applications.

General Features

- $V_{DS} = -20V$, $I_D = -90A$

$R_{DS(ON)} < 2.3m\Omega$ @ $V_{GS}=-10V$

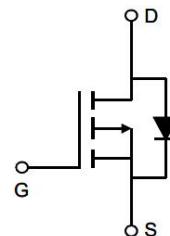
$R_{DS(ON)} < 2.5m\Omega$ @ $V_{GS}=-4.5V$

$R_{DS(ON)} < 3.7m\Omega$ @ $V_{GS}=-2.5V$

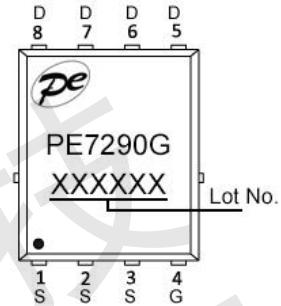
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation

Application

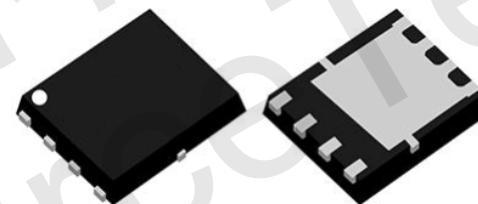
- PWM applications
- Load switch
- Battery protection



Schematic diagram



Marking and pin assignment



DFN5x6-8L

Absolute Maximum Ratings ($TC=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous ($TC=25^\circ C$)	I_D	-90	A
Drain Current-Continuous ($TC=70^\circ C$)	I_D	-68	A
Maximum Power Dissipation ($TC=25^\circ C$)	P_D	156	W
Pulsed Drain Current (Note 1)	I_{DM}	-360	A
Drain Current-Continuous ($TA=25^\circ C$)	I_D	-44	A
Drain Current-Continuous ($TA=70^\circ C$)	I_D	-35	A
Maximum Power Dissipation ($TA=25^\circ C$)	P_D	5	W
Avalanche Current	I_{AS}	94	A
Avalanche Energy ($L=0.1mH$)	E_{AS}	440	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.8	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	25	°C/W



Electrical Characteristics (TC=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-18V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.7	-1.05	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-20A$	-	1.9	2.3	$m\Omega$
		$V_{GS}=-4.5V, I_D=-20A$	-	2	2.5	$m\Omega$
		$V_{GS}=-2.5V, I_D=-15A$	-	2.5	3.7	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-20A$	-	100	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V, F=1.0MHz$	-	14250	-	pF
Output Capacitance	C_{oss}		-	1810	-	pF
Reverse Transfer Capacitance (Note 4)	C_{rss}		-	1765	-	pF
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-10V, R_L=1\Omega, V_{GS}=-10V, R_G=3\Omega$	-	11	-	nS
Turn-on Rise Time	t_r		-	27	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	340	-	nS
Turn-Off Fall Time	t_f		-	130	-	nS
Total Gate Charge	Q_g	$V_{DS}=-10V, I_D=-20A, V_{GS}=-4.5V$	-	310	-	nC
Gate-Source Charge	Q_{gs}		-	24	-	nC
Gate-Drain Charge	Q_{gd}		-	75.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-1A$	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-90	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to product.



Typical Electrical and Thermal Characteristics

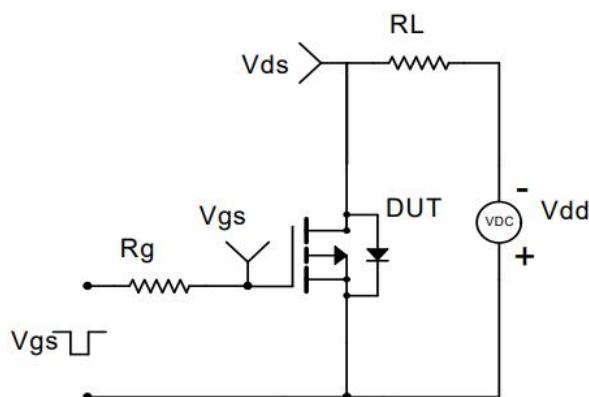


Figure 1 Switching Test Circuit

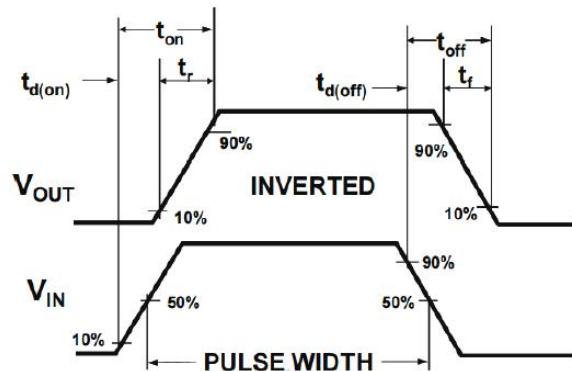
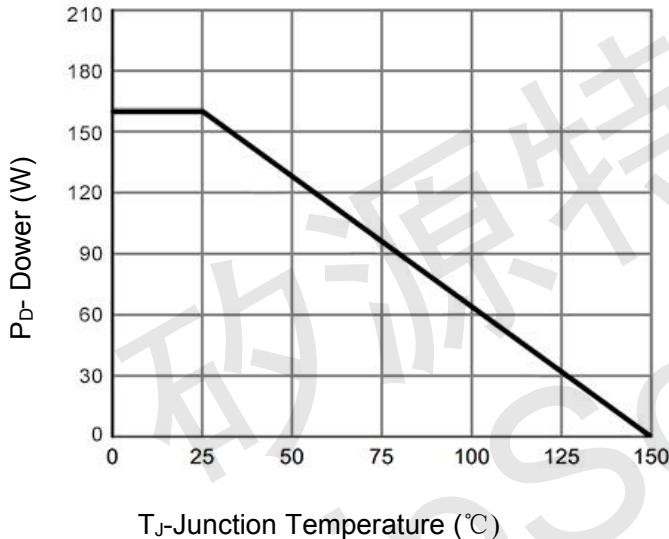
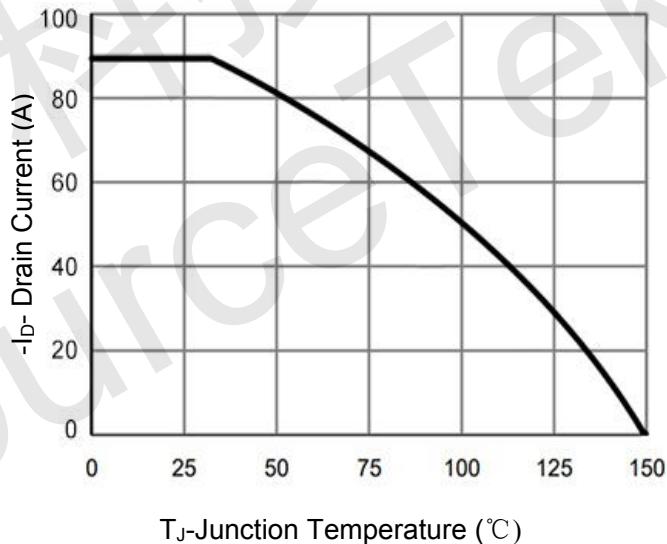


Figure 2 Switching Waveform



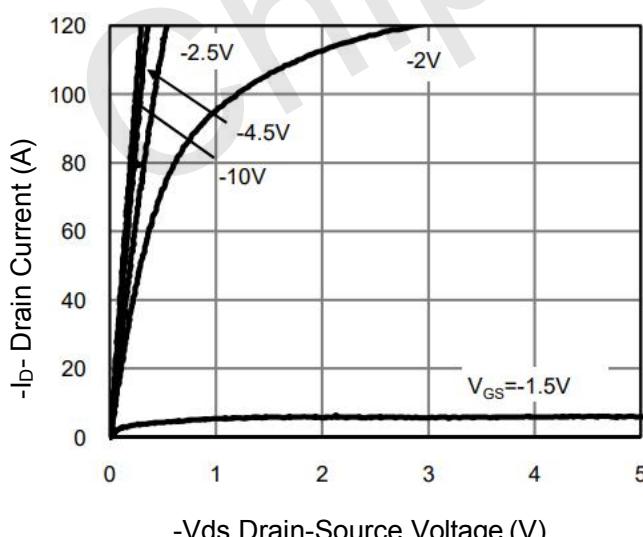
T_J-Junction Temperature (°C)

Figure 3 Power De-rating



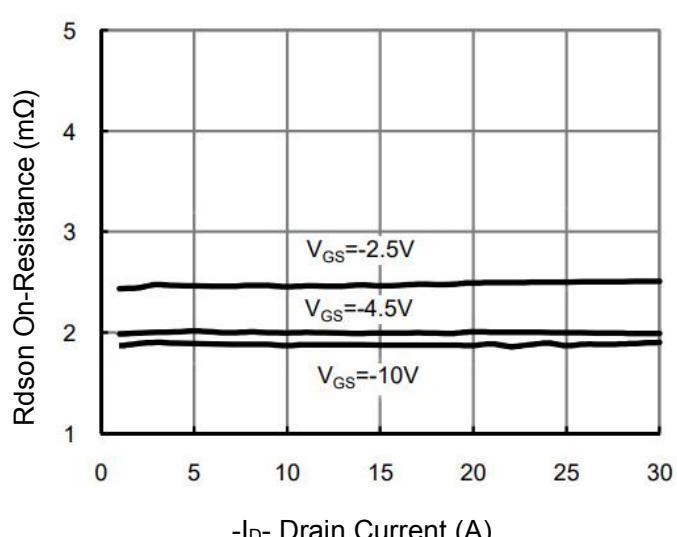
T_J-Junction Temperature (°C)

Figure 4 Drain Current



-Vds Drain-Source Voltage (V)

Figure 5 Output Characteristics



-I_D- Drain Current (A)

Figure 6 Rdson vs Drain Current

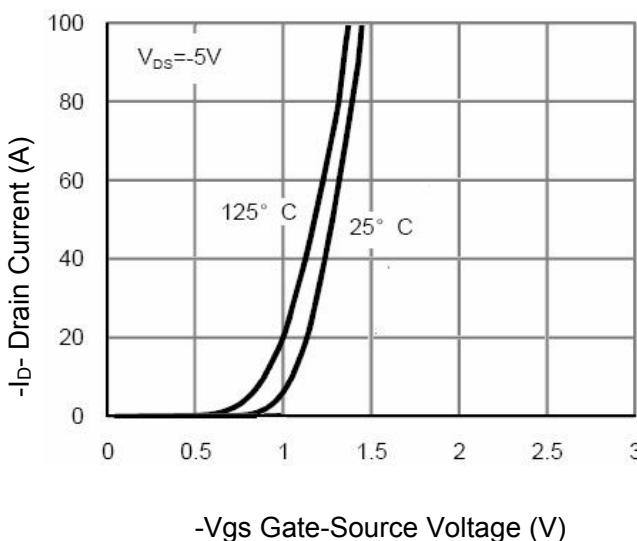


Figure 7 Transfer Characteristics

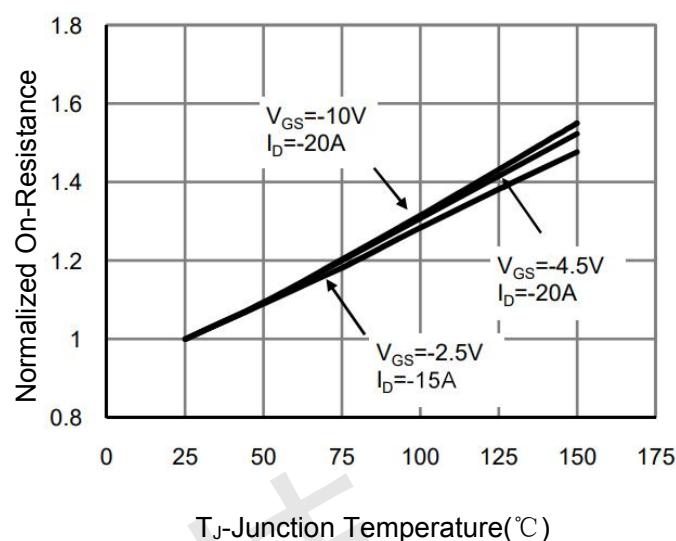


Figure 8 R_{DSON} vs Junction Temperature

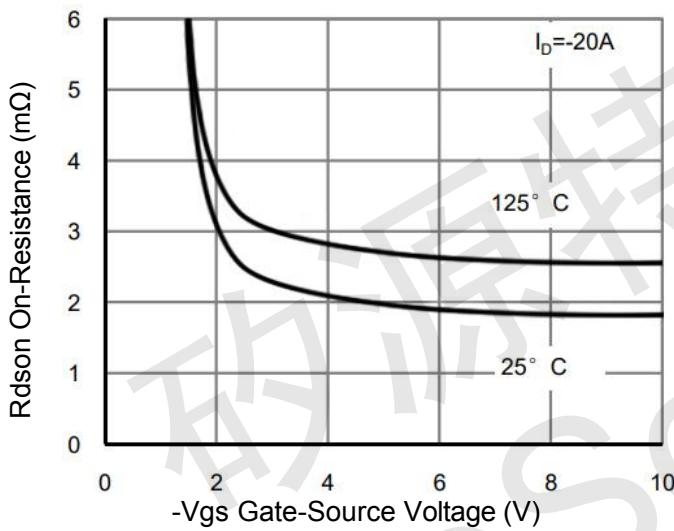


Figure 9 R_{DSON} vs V_{GS}

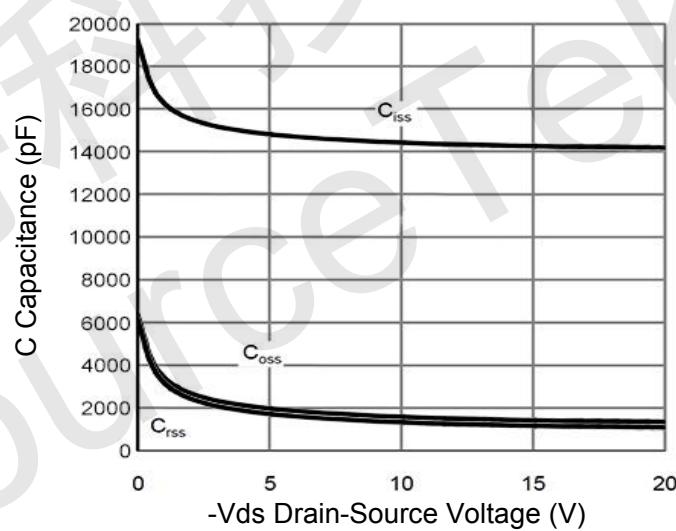


Figure 10 Capacitance vs V_{DS}

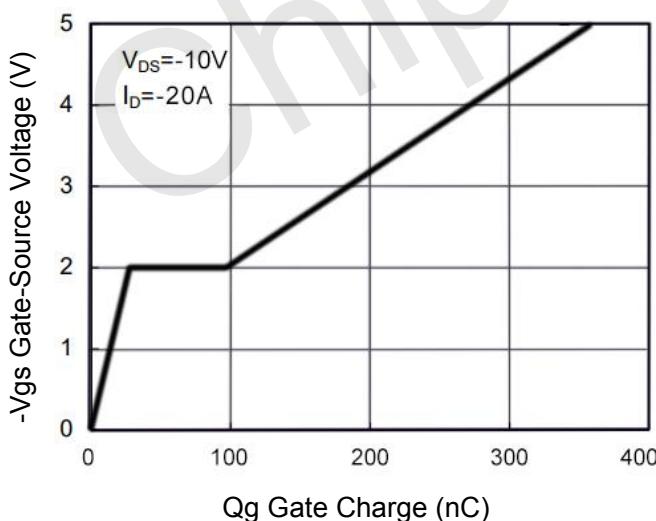


Figure 11 Gate Charge

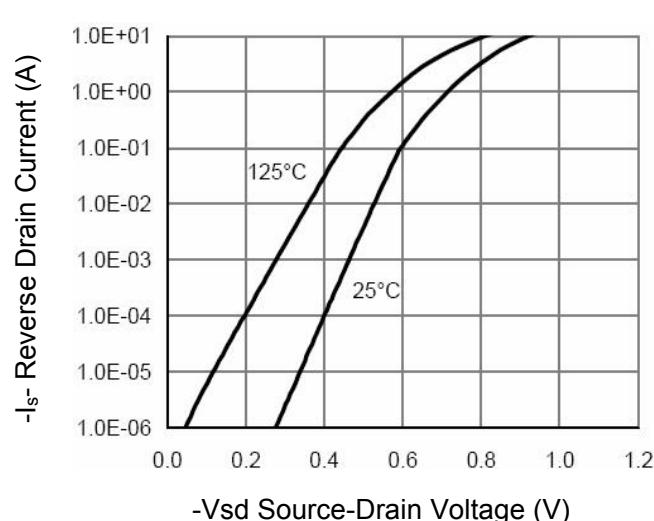


Figure 12 Source- Drain Diode Forward

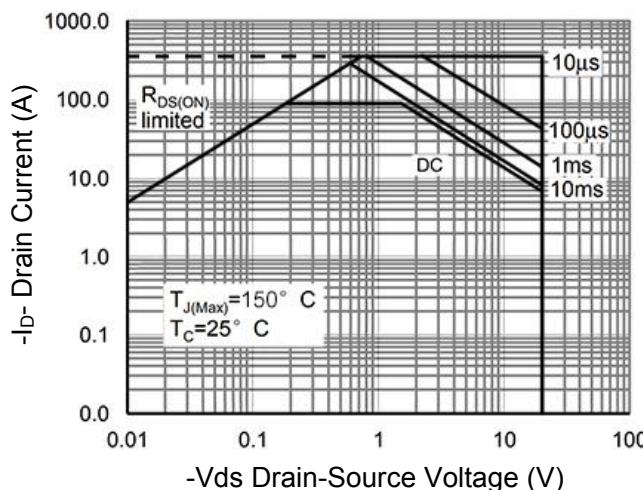


Figure 13 Safe Operation Area

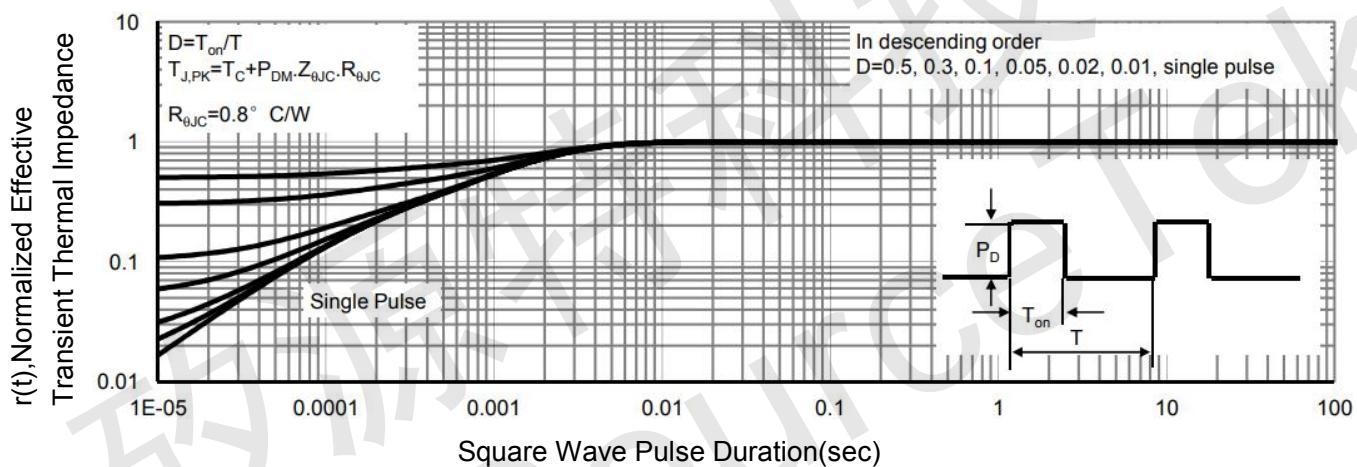
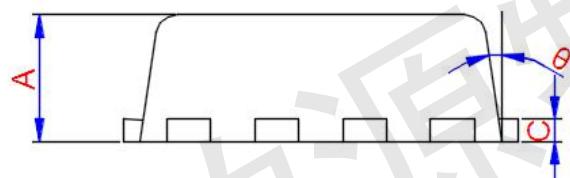
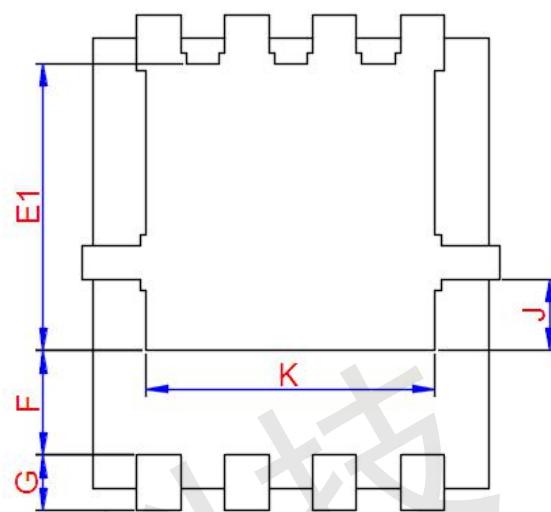
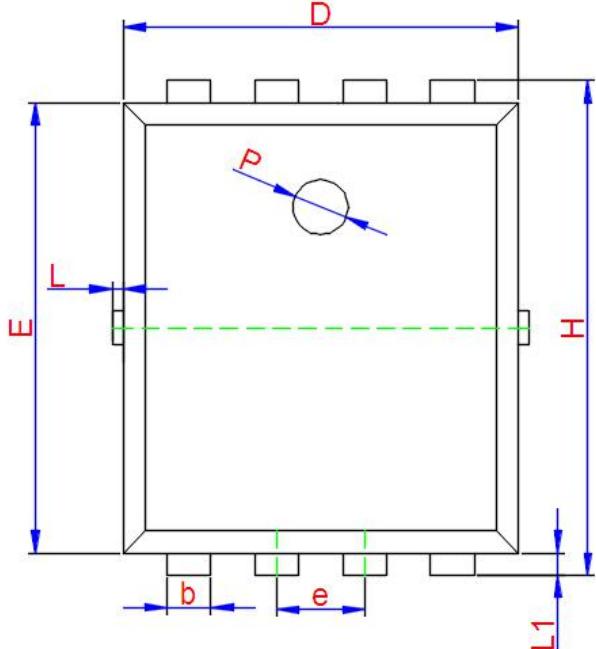


Figure 14 Normalized Maximum Transient Thermal Impedance



DFN5x6-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	0.800	0.900	1.000
b	0.350	0.420	0.490
c	0.254TYP.		
D	4.900	5.000	5.100
e	1.270TYP.		
E	5.700	5.800	5.900
E1	3.400TYP.		
F	1.400TYP.		
G	0.600TYP.		
H	5.950	6.080	6.200
J	0.950TYP.		
K	4.000TYP		
L	-	-	0.150
L1	0.100	0.140	0.180
P	1.000TYP.		
θ	6°	10°	14°